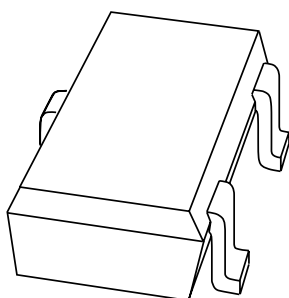


DATA SHEET



BAV70W

High-speed double diode

Product specification
Supersedes data of 1999 May 05

2002 Apr 05

High-speed double diode

BAV70W

FEATURES

- Very small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

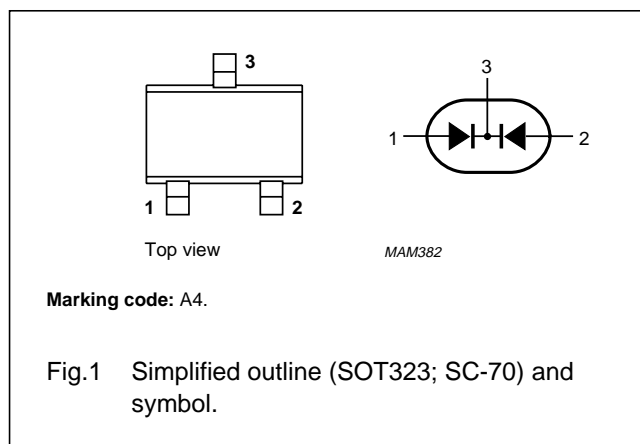
- High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

The BAV70W consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the very small SOT323 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	anode (a1)
2	anode (a2)
3	common cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	single diode loaded; note 1; see Fig.2	–	175	mA
		double diode loaded; note 1; see Fig.2	–	100	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4			
		$t = 1\text{ }\mu\text{s}$	–	4	A
		$t = 1\text{ ms}$	–	1	A
		$t = 1\text{ s}$	–	0.5	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

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ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V_F	forward voltage	see Fig.3 $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$ $I_F = 50\text{ mA}$ $I_F = 150\text{ mA}$	715 855 1 1.25	mV mV V V
I_R	reverse current	see Fig.5 $V_R = 25\text{ V}$ $V_R = 75\text{ V}$ $V_R = 25\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$ $V_R = 75\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	30 2.5 60 100	nA μA μA μA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	1.5	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10\text{ mA}$; $t_r = 20\text{ ns}$; see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		300	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

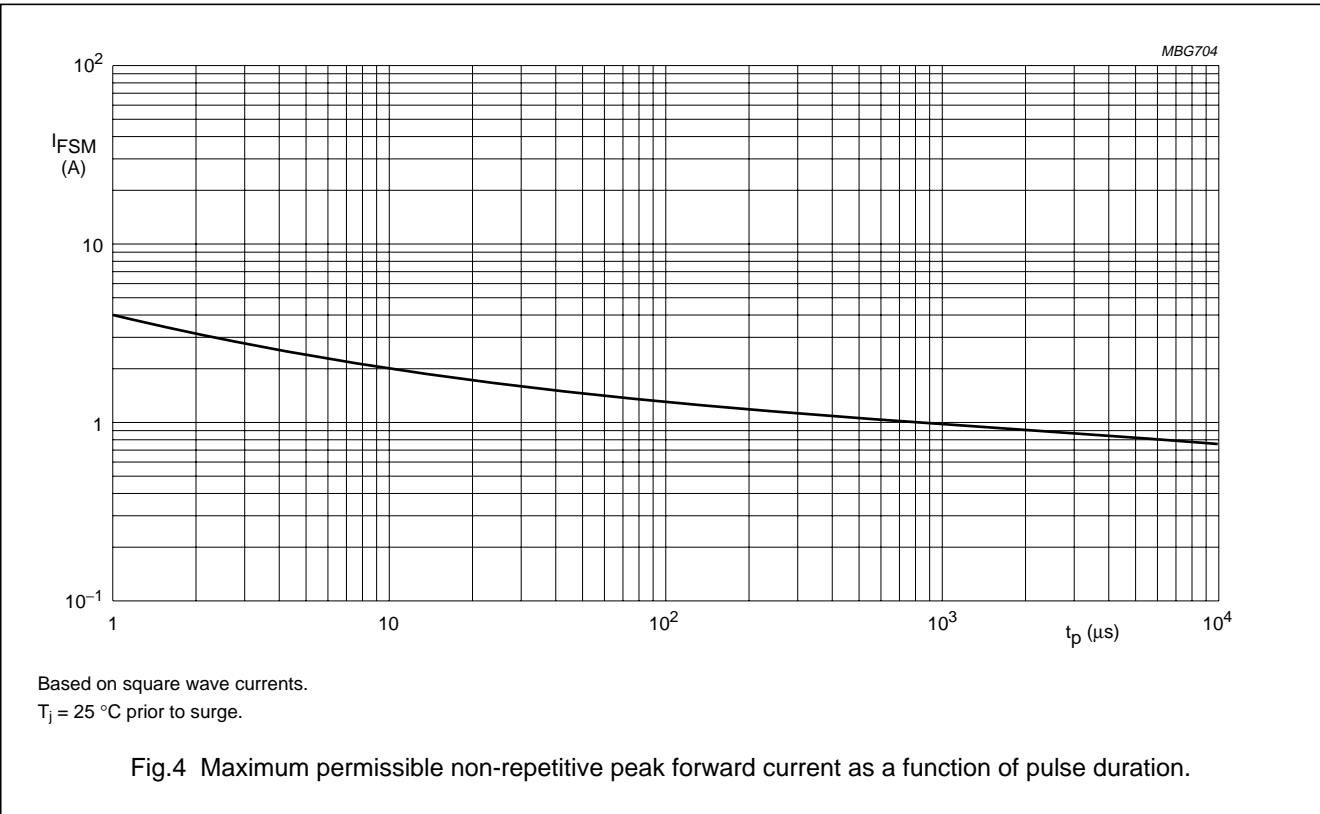
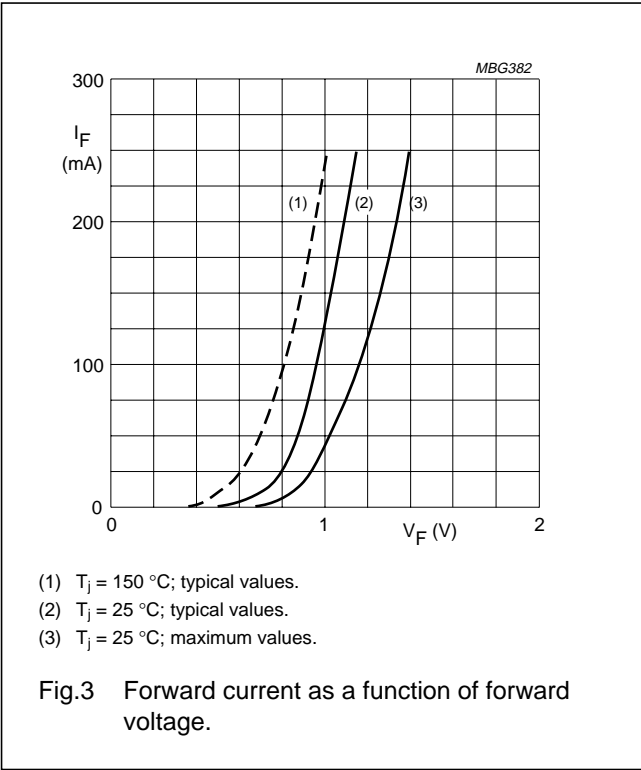
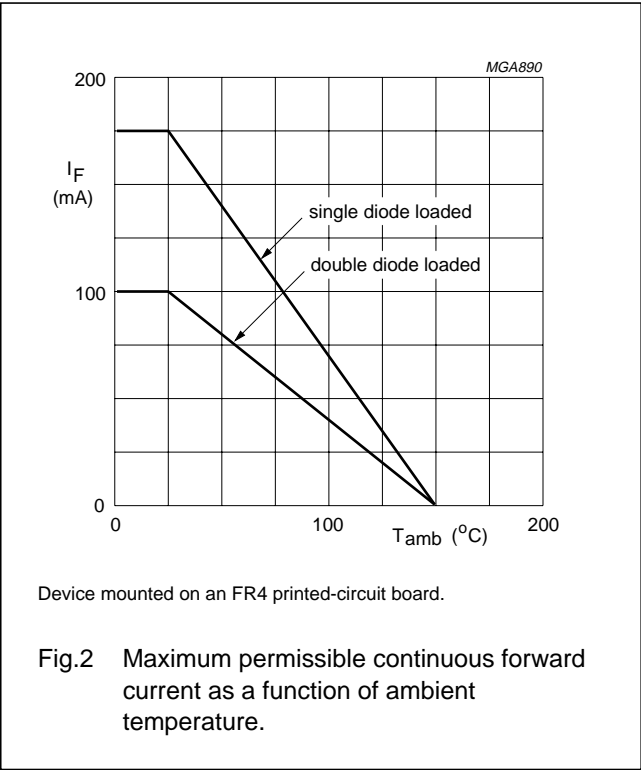
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

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GRAPHICAL DATA



High-speed double diode

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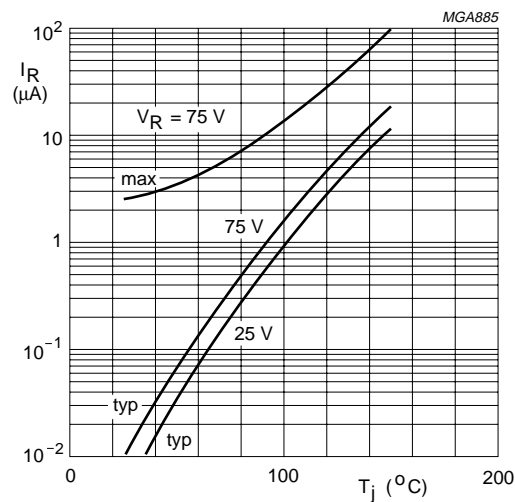
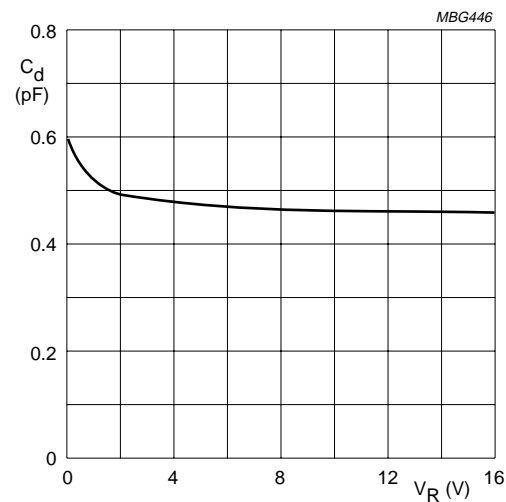


Fig.5 Reverse current as a function of junction temperature.

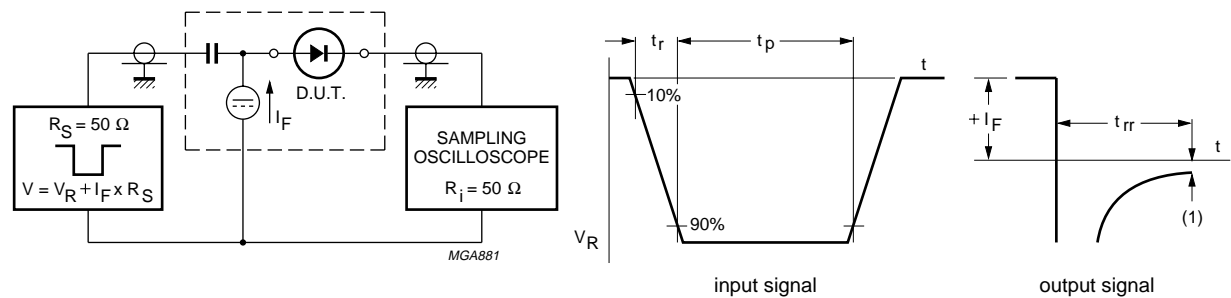


$f = 1 \text{ MHz}; T_j = 25^{\circ}C$.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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(1) $I_R = 1\text{ mA}$.

Fig.7 Reverse recovery voltage test circuit and waveforms.

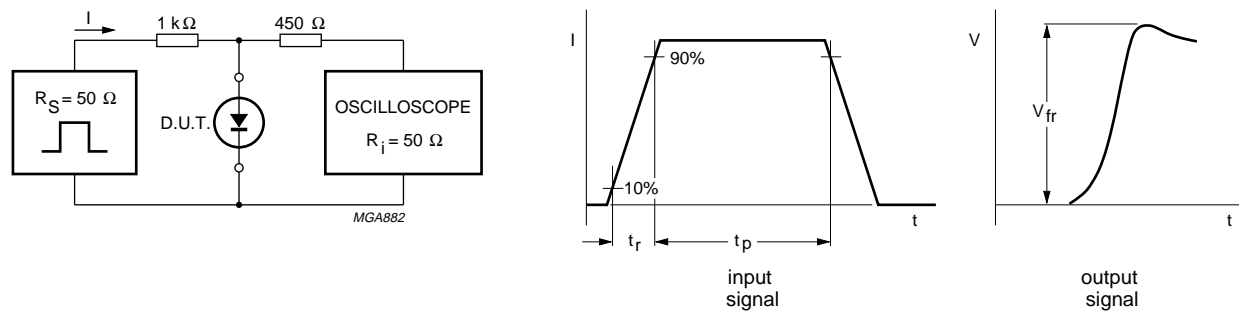


Fig.8 Forward recovery voltage test circuit and waveforms.

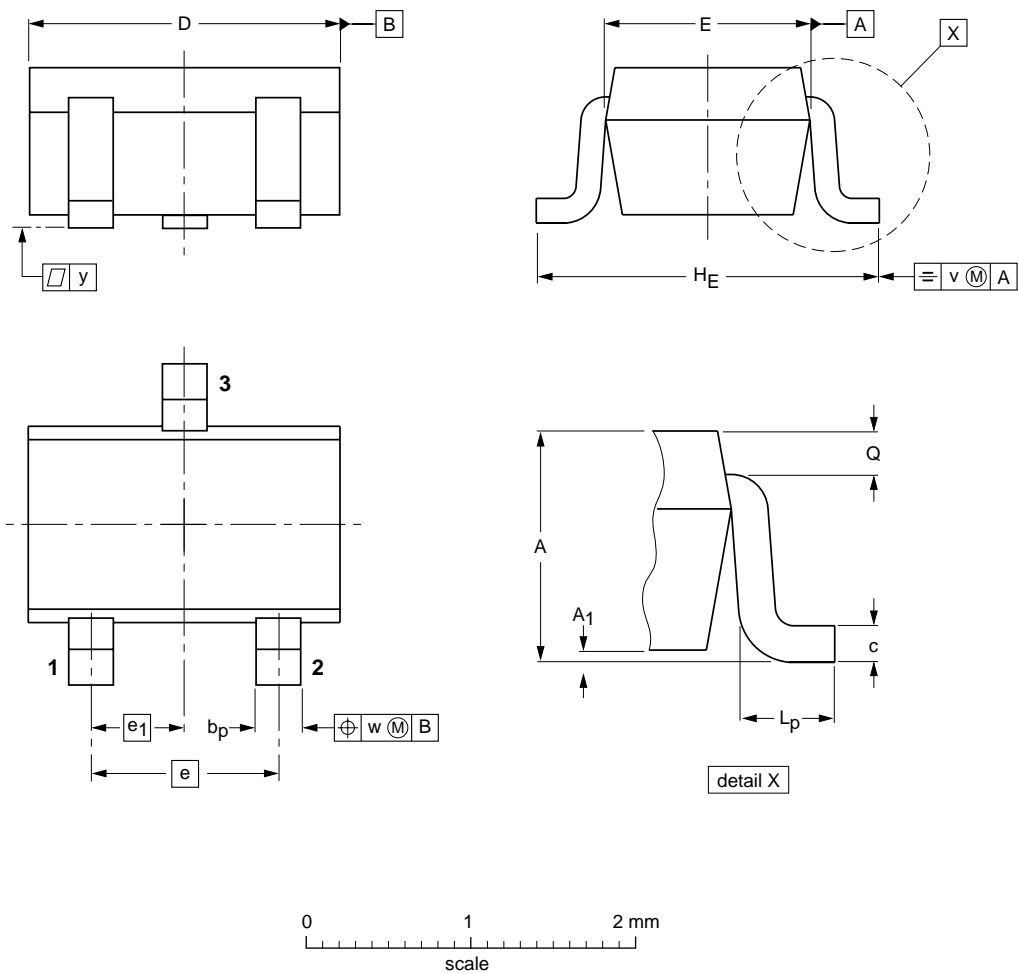
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1max	bp	c	D	E	e	e1	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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NOTES

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